

B11G1822N60D

LDMOS 2-stage integrated Doherty MMIC

Rev. 2 — 7 April 2022

AMPLEON

Product data sheet

1. Product profile

1.1 General description

The B11G1822N60D is a dual section 2-stage fully integrated Doherty MMIC solution using Ampleon's state of the art LDMOS technology. The carrier and peaking device, input splitter, output combiner and pre-match are integrated in each section. This multiband device is perfectly suited as general purpose driver in the frequency range 1800 MHz to 2200 MHz. Available in PQFN outline.

Table 1. Application performance

Typical RF performance at $T_{case} = 25\text{ °C}$; $I_{DQ} = 150\text{ mA}$ (carrier and peaking);

$V_{GSq(peaking)} = V_{GSq(carrier)} - 0.47\text{ V}$. Test signal: 1-carrier LTE 20 MHz; PAR = 7.6 dB; measured in an Ampleon $f = 2000\text{ MHz}$ combined integrated Doherty application circuit.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	η _D
	(MHz)	(V)	(W)	(dB)	(%)
1-carrier LTE 20 MHz PAR = 7.6 dB	2000	28	5	29.8	29.5

1.2 Features and benefits

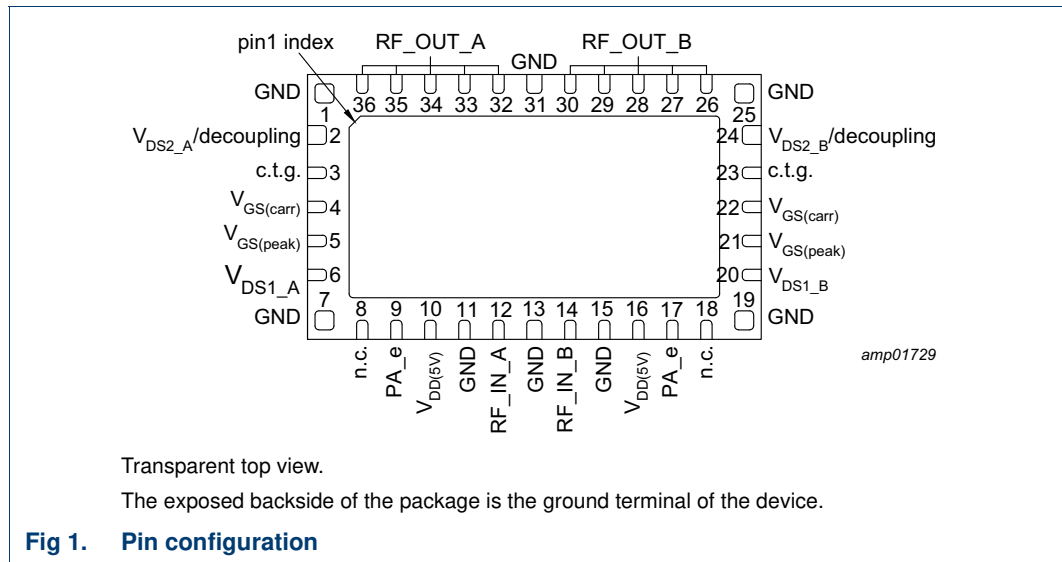
- Integrated input splitter
- Integrated output combiner
- 20 Ω output impedance thanks to integrated pre-match
- High linearity
- Designed for large RF and instantaneous bandwidth operation
- Independent control of carrier and peaking bias
- Integrated bias gate switch
- Integrated ESD protection
- Source impedance 50 Ω; high power gain
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

- Macrocell base station driver
- Microcell base station
- 5G mMIMO
- W-CDMA/LTE
- Active antenna
- General purpose applications

2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
GND	1	ground
$V_{DS2_A}/decoupling$	2	drain-source voltage of final stages of section A
c.t.g.	3	connect to ground
$V_{GS(carr)}$	4	gate-source voltage of carrier [1]
$V_{GS(peak)}$	5	gate-source voltage of peaking [2]
V_{DS1_A}	6	drain-source voltage of driver stages of section A
GND	7	ground
n.c.	8	not connected
PA_e	9	PA enable trigger signal, 0 V to 5 V, I_{Dq} -bias ON/OFF corresponds to logic HIGH/LOW [3]
$V_{DD(5V)}$	10	supply voltage (5 V) [4]
GND	11	ground
RF_IN_A	12	RF input of section A
GND	13	ground
RF_IN_B	14	RF input of section B
GND	15	ground
$V_{DD(5V)}$	16	supply voltage (5 V) [4]
PA_e	17	PA enable trigger signal, 0 V to 5 V, I_{Dq} -bias ON/OFF corresponds to logic HIGH/LOW [3]
n.c.	18	not connected
GND	19	ground

Table 2. Pin description ...continued

Symbol	Pin	Description
V_{DS1_B}	20	drain-source voltage of driver stages of section B
$V_{GS(peak)}$	21	gate-source voltage of peaking [2]
$V_{GS(carr)}$	22	gate-source voltage of carrier [1]
c.t.g.	23	connect to ground
$V_{DS2_B}/decoupling$	24	drain-source voltage of final stages of section B
GND	25	ground
RF_OUT_B	26, 27, 28, 29, 30	RF output of section B
GND	31	ground
RF_OUT_A	32, 33, 34, 35, 36	RF output of section A

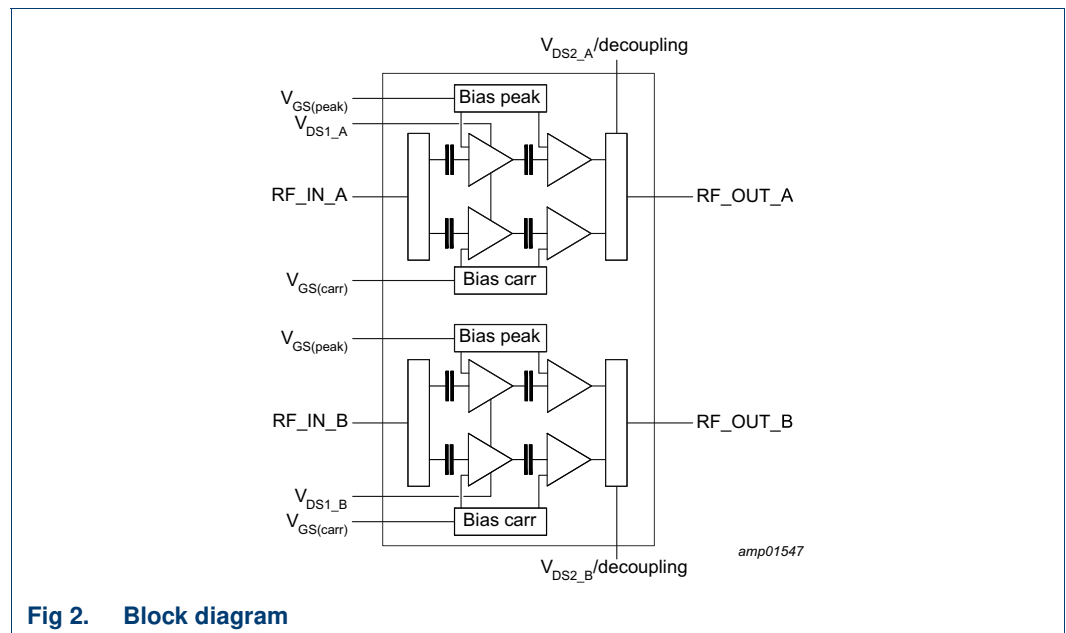
- [1] Pins connected together.
- [2] Pins connected together.
- [3] Pins connected together.
- [4] Pins connected together.

3. Ordering information

Table 3. Ordering information

Package name	Orderable part number	12NC	Packing description	Min. orderable quantity (pieces)
PQFN-12x7-36-1	B11G1822N60DX	9349 604 67525	TR13; 1500-fold; 24 mm; dry pack	1500
PQFN-12x7-36-1	B11G1822N60DYZ	9349 604 67535	TR7; 300-fold; 24 mm; dry pack	300

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature	[1]	-	200	°C

[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics

Measured for total device.

Symbol	Parameter	Conditions	Value	Unit	
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case} = 90\text{ °C}$			
		$P_L = 5\text{ W}$	[1]	2.45	K/W
		$P_L = 10\text{ W}$	[1]	2.1	K/W

[1] When operated with a 1-carrier W-CDMA with PAR = 9.9 dB.

7. Characteristics

Table 6. DC characteristics

$T_{case} = 25\text{ °C}$; $V_{DD(5V)} = 5\text{ V}$; $V_{on(PA_e)} = 5\text{ V}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Carrier						
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28\text{ V}$; $I_D = 150\text{ mA}$	1.7	2.1	2.6	V
I_{GSS}	gate leakage current	$V_{GS} = 2\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	140	nA
Peaking						
I_{GSS}	gate leakage current	$V_{GS} = 2\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	140	nA
Final stages						
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}$; $V_{DS} = 28\text{ V}$	-	-	1.4	μA
Driver stages						
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}$; $V_{DS} = 28\text{ V}$	-	-	1.4	μA

Table 7. RF characteristics

Typical RF performance at $T_{case} = 25\text{ °C}$; $V_{DS} = 28\text{ V}$; $I_{DQ} = 150\text{ mA}$ (carrier); $f = 2000\text{ MHz}$; $V_{DD(5V)} = 5\text{ V}$; $V_{on(PA_e)} = 4.8\text{ V}$; $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.5\text{ V}$; $P_{L(AV)} = 5\text{ W}$; unless otherwise specified, measured in an Ampleon combined production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Test signal: pulsed CW [1]						
G_p	power gain	$P_L = 5\text{ W}$ (37 dBm)	26	29	32	dB
η_D	drain efficiency	$P_L = 5\text{ W}$ (37 dBm)	20	29	-	%
		$P_L = P_{L(3dB)}$	43	53	-	%
RL_{in}	input return loss		-	-15	-10	dB
$P_{L(3dB)}$	output power at 3 dB gain compression		47.0	48.5	-	dBm

[1] Pulsed CW power sweep measurement ($\delta = 10\%$, $t_p = 100\text{ }\mu\text{s}$).

8. Application information

8.1 Typical performance

Table 8. Typical performance

$T_{case} = 25\text{ °C}$; $V_{DS} = 28\text{ V}$; $I_{DQ} = 150\text{ mA}$ (carrier and peaking); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.47\text{ V}$; $V_{DD(5V)} = 5\text{ V}$; $V_{on(PA_e)} = 5\text{ V}$. Test signal: 1-carrier W-CDMA; PAR = 9.9 dB; unless otherwise specified, measured in an Ampleon 1800 MHz to 2200 MHz frequency band combined application circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(1dB)}$	output power at 1 dB gain compression	$f = 2000\text{ MHz}$ [1]	-	48.5	-	dBm
$\varphi_{s21}/\varphi_{s21(norm)}$	normalized phase response	at 1 dB compression point; $f = 2000\text{ MHz}$ [2]	-	-2.3	-	°
η_D	drain efficiency	12.2 dB OBO ($P_{L(AV)} = 37\text{ dBm}$); $f = 2000\text{ MHz}$	-	29.5	-	%
G_p	power gain	$P_{L(AV)} = 37\text{ dBm}$; $f = 2000\text{ MHz}$	-	29.8	-	dB
B_{video}	video bandwidth	$P_{L(AV)} = 37\text{ dBm}$ set to obtain $IMD3 = -45\text{ dBc}$; $f = 2000\text{ MHz}$	-	406	-	MHz
G_{flat}	gain flatness	$P_{L(AV)} = 37\text{ dBm}$; $f = 1800\text{ MHz}$ to 2200 MHz	-	1	-	dB
$ACPR_{20M}$	adjacent channel power ratio (20 MHz)	$P_{L(AV)} = 37\text{ dBm}$; $f = 2000\text{ MHz}$	-	-42.1	-	dBc
$\Delta G/\Delta T$	gain variation with temperature	$f = 2000\text{ MHz}$	-	0.046	-	dB/°C
K	Rollett stability factor	$T_{case} = -40\text{ °C}$; $f = 0.1\text{ GHz}$ to 6 GHz [3]	-	>1	-	
Bias gate switch						
t_r	rise time	$Z_S = 500\text{ }\Omega$ (max); $T_{case} = -40\text{ °C}$ to $+120\text{ °C}$; $V_{on(PA_e)} \geq 4.8\text{ V}$ [4]	-	200	-	ns
t_f	fall time	$T_{case} = -40\text{ °C}$ to $+120\text{ °C}$; $V_{off(PA_e)} \leq 1\text{ V}$ [5]	-	80	-	ns

[1] Pulsed CW power sweep measurement ($\delta = 10\%$, $t_p = 100\text{ }\mu\text{s}$).

[2] 25 ms CW power sweep measurement.

[3] With input VSWR better than 12 : 1.

[4] RF output rise time 10 % to 90 % RF power.

[5] RF output fall time 90 % to 10 % RF power.

8.2 PCB layout and electrical schematic

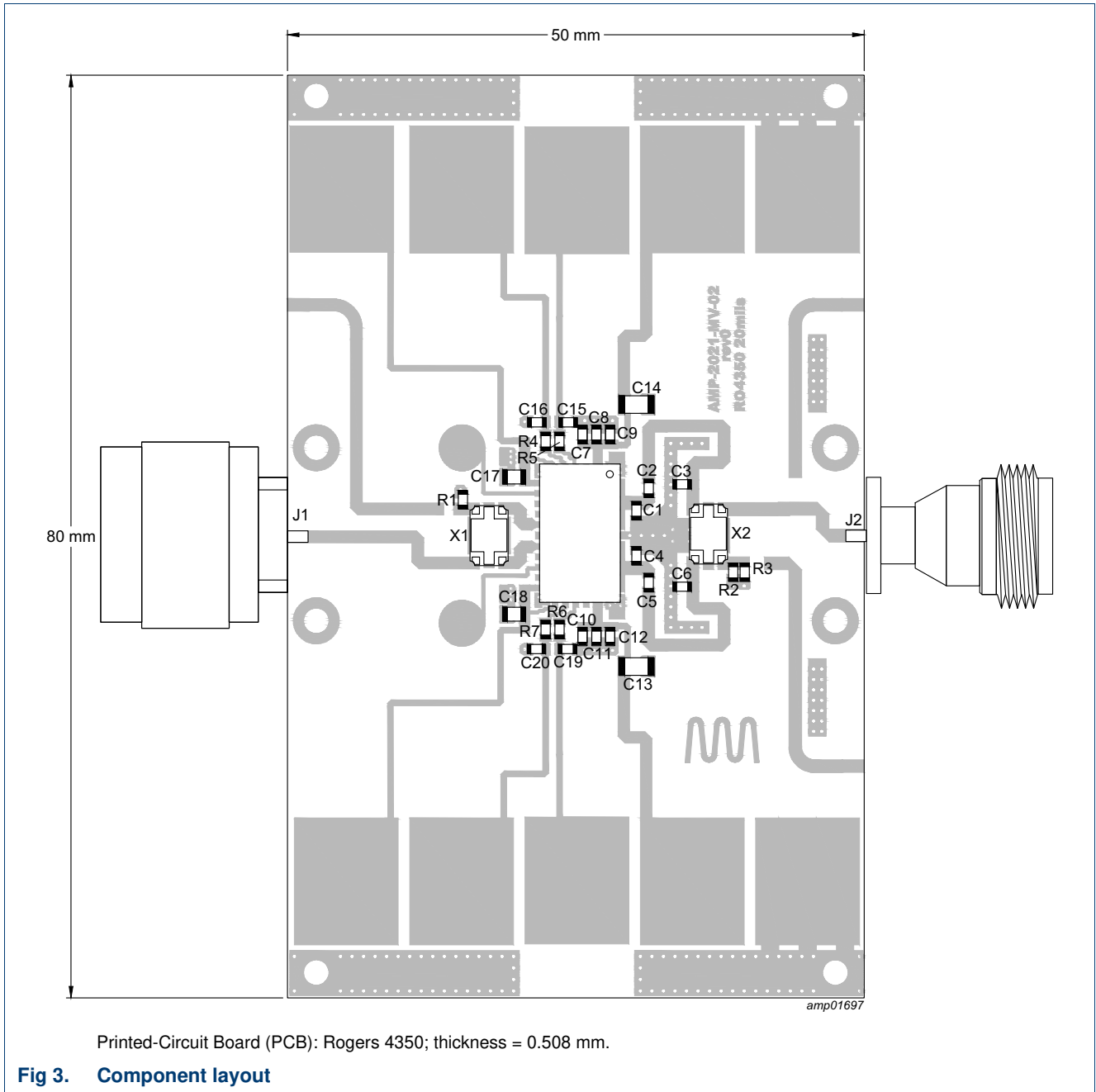


Table 9. Demo test circuit list of components

See [Figure 3](#) for component layout.

Component	Description	Value	Remarks
C1, C4	multilayer ceramic chip capacitor	1.6 pF, ± 0.1 %	Murata: GQM1875C2E1R6BB12
C2, C5	multilayer ceramic chip capacitor	3.3 pF, ± 0.1 %	Murata: GQM1875C2E3R3BB12
C3, C6	multilayer ceramic chip capacitor	0.6 pF, ± 0.1 %	Murata: GQM1875C2ER60BB12
C7, C8, C9, C10, C11, C12	multilayer ceramic chip capacitor	100 nF, 50 V	Murata: 06035C104KAT2A

Table 9. Demo test circuit list of components ...continued
See [Figure 3](#) for component layout.

Component	Description	Value	Remarks
C13, C14	multilayer ceramic chip capacitor	1 μ F, 50 V	Murata: GRM21BR6YA106KE43
C15, C16, C17, C18, C19, C20	multilayer ceramic chip capacitor	1 μ F, 50 V	Murata: C1608X5R1H105K080AB
R1	resistor	49.9 Ω , $\pm 1\%$, 100 mW	Multicomp Pro: MCWF06R49R9BTL
R2, R3	resistor	100 Ω , $\pm 1\%$, 200 mW	Multicomp Pro: MP001293
R4, R5, R6, R7	resistor	1 k Ω , $\pm 1\%$, 100 mW	Multicomp Pro: MCSR06X1001FTL
X1, X2	hybrid coupler	1.7 GHz – 2.3 GHz, 25 W	Anaren: X3C19F1-03S
J1	N Coaxial panel connector male		Radiall: R161.438.200
J2	N Coaxial panel connector female		Huber & Suhner: 23_N-50-0-16/133_NE

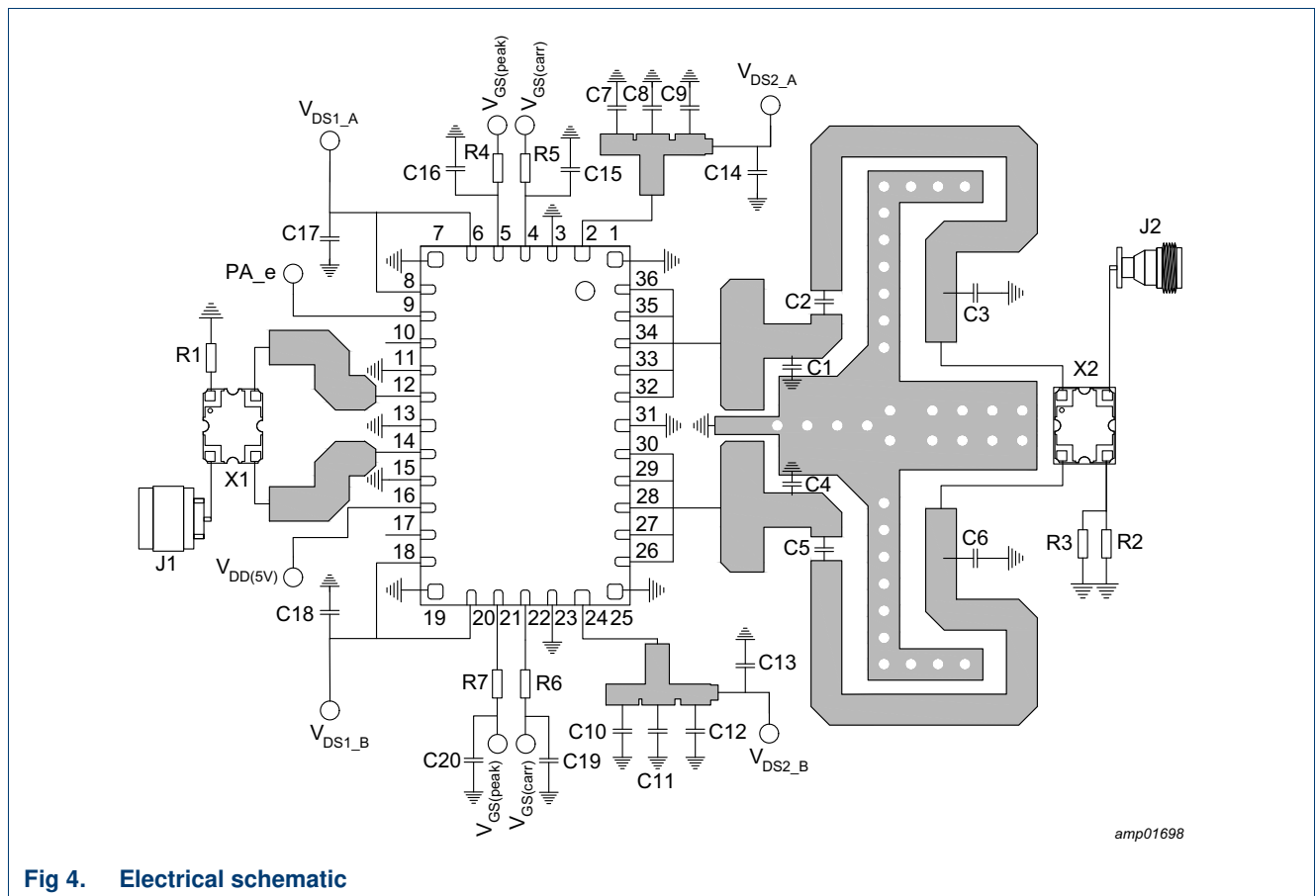


Fig 4. Electrical schematic

8.3 Recommendations

- RC circuit at gate bias must be implemented to insure improved linearity and stability of the circuit. The implementation has to be symmetrical between both amplifier sections Pin 5/21 and Pin 4/22.
- In TDD mode controlled by an external bias switch, the outputs of the switches must be connected on both amplifier sections. As shown in Fig.4, gate bias supply must be connected before RC circuit of Pin 5/21 and Pin 4/22 respectively by default.

8.4 Ruggedness in a Doherty operation

8.4.1 Output mismatch ruggedness

The B11G1822N60D is capable of withstanding a load mismatch corresponding to $V_{SWR} = 10 : 1$ through all phases under the following conditions: $V_{DS} = 32 \text{ V}$; $I_{Dq} = 82 \text{ mA}$ (carrier); $V_{GSq(peak)} = V_{GSq(carrier)} - 0.48 \text{ V}$; $V_{DD(5V)} = 5 \text{ V}$; $V_{on(PA_e)} = 5 \text{ V}$; P_i corresponding to $P_{L(3dB)} - 9 \text{ dB}$ under $Z_S = 50 \Omega$ load; $f = 2200 \text{ MHz}$ (1-carrier W-CDMA); $T_{case} = 25 \text{ }^\circ\text{C}$; per section.

8.4.2 Wideband noise ruggedness

The B11G1822N60D is capable of withstanding an AWGN (Additive White Gaussian Noise) with 11.2 dB PAR, OBW (Occupied BandWidth) of 900 MHz, under the following conditions: $V_{DS} = 32 \text{ V}$; $I_{Dq} = 82 \text{ mA}$ (carrier); $V_{GSq(peak)} = V_{GSq(carrier)} - 0.5 \text{ V}$; $V_{DD(5V)} = 5 \text{ V}$; $V_{on(PA_e)} = 5 \text{ V}$; 3 dB P_i overdrive from $P_{L(AV)} = 34 \text{ dBm}$ (corresponding to $P_{L(3dB)} - 12 \text{ dB OBO}$); $f = 2000 \text{ MHz}$; $T_{case} = 25 \text{ }^\circ\text{C}$; per section.

8.5 Impedance information

Table 10. Typical impedance for optimum Doherty operation

Measured load-pull data per section; test signal: pulsed CW; $T_{case} = 25 \text{ }^\circ\text{C}$; $V_{DS} = 28 \text{ V}$; $I_{Dq} = 75 \text{ mA}$ (carrier); $V_{GSq(peak)} = V_{GSq(carrier)} - 0.46 \text{ V}$; $V_{DD(5V)} = 5 \text{ V}$; $V_{on(PA_e)} = 5 \text{ V}$; $t_p = 100 \mu\text{s}$; $\delta = 10 \%$.

f (MHz)	tuned for optimum Doherty operation				
	Z_L [1] (Ω)	$P_{L(1dB)}$ (dBm)	$G_{p(max)}$ (dB)	η_{add} [2] (%)	η_{add} [3] (%)
1700	5.46 – j13.87	45.02	30.84	48.87	28.96
1800	7.57 – j14.37	45.28	31.52	52.56	29.35
1900	8.75 – j14.21	45.41	31.04	52.83	29.27
2000	11.96 – j12.04	45.31	31.33	54.37	29.35
2100	11.77 – j11.62	45.33	31.73	56.47	29.72
2200	11.88 – j13.08	45.27	31.58	57.36	29.18
2300	11.97 – j13.33	44.90	30.50	57.46	28.96

[1] Reference package plane.

[2] At $P_{L(1dB)}$.

[3] At 34 dBm.

9. Package outline

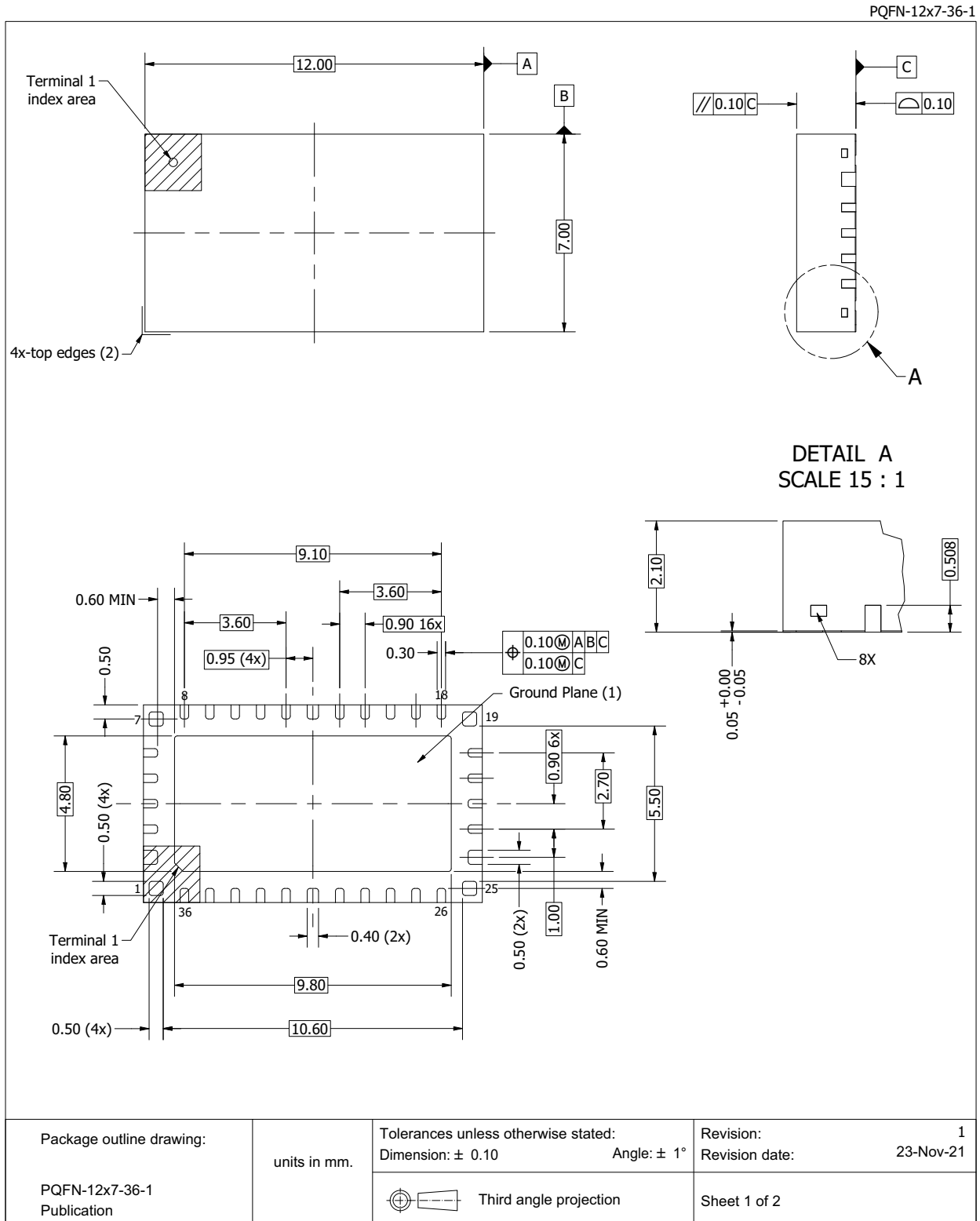


Fig 5. Package outline PQFN-12x7-36-1 (sheet 1 of 2)

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.
Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1C [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V.
- [2] HBM classification 1C is granted to any part that passes after exposure to an ESD pulse of 1000 V.

11. Abbreviations

Table 12. Abbreviations

Acronym	Description
5G	Fifth Generation
CW	Continuous Wave
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LTE	Long Term Evolution
MMIC	Monolithic Microwave Integrated Circuit
mMIMO	massive Multiple Input Multiple Output
MTF	Median Time to Failure
OBO	Output Back Off
PA	Power Amplifier
PAR	Peak-to-Average power Ratio
RC	resistor-capacitor
RoHS	Restriction of Hazardous Substances
TDD	Time Division Duplex
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

12. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
B11G1822N60D v.2	20220407	Product data sheet	-	B11G1822N60D v.1
Modifications:	<ul style="list-style-type: none"> • Table 3 on page 3: added second orderable part number • Section 13.2 on page 13: updated section • Section 13.3 on page 13: updated section 			
B11G1822N60D v.1	20211217	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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